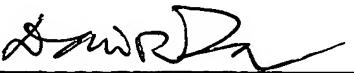




Form PTO-1449 (Modified) <small>10/03/02</small>				Atty Docket No.:	Serial No.:			
				03692.P059DC	10/722,792			
List of Patents and Publications Statement (Use several sheets if necessary)				Applicants:				
				Disney, D.				
				Filing Date: November 25, 2003				
REFERENCE DESIGNATION			U.S. PATENT DOCUMENTS					
Exam. Initial		Date	Document Number	Name	Class	Sub-Class	Filing Date	
FOREIGN PATENT DOCUMENTS								
No.		Document No.	Date	Country	Name	Class	Sub-Class	Trans-lation
JP	JP 56-38867	04/14/81	Japan	Okabe, T., et al.				English
JP	JP 57-10975	01/20/82	Japan	Sanyo				
W/O	W/O 99/34449	07/08/99	PCT	Konin Klijke				
JP	JP 57-12557	01/22/82	Japan	Tanaka, T., et al.				
JP	JP 57-12558	01/22/82	Japan	Tanaka, T., et al.				
JP	JP 60-64471	04/13/85	Japan	Saiotou, M.				
JP	JP 3-211771	09/17/91	Japan	Toshiba				
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)								
JP		International Electron Device Meeting 1979 – Washington, D.C., Dec. 3-4-5, Sponsored by Electron Devices Society of IEEE, Pages 238-241						
JP		"Realization of High Breakdown Voltage (>700V) in Thin SOI Devices" S. Merchant, et al., Phillips Laboratories North American Phillips Corporation 1991 IEEE, Pages 31-35						
Examiner				Date Considered				
<i>David</i>				9/28/04				
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

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DR		JP 4107877A	04/09/92	Japan	Yamanishi, et al.			
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		DE 43 09 764	09/29/94	Germany	Tihanyi, et al.			
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		W/O 97 35346	11/25/97	PCT	Tihanyi			
		W/O 00 33385	06/08/00	PCT	Tihanyi			
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Examiner				Date Considered				
<i>David D.</i>				9/28/04				
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PN		W/O 02 099909	12/12/02	PCT	Liang, et al.			
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1		"Comparison of High-Voltage Devices for Power Integrated Circuits," R. Jay Anaman, et al., IEDM 84, Pages 258-261						
PN		"A New Generation of High-Voltage MOSFET's Breaks the Limit Line of Silicon," G. Debby, et al., Siemens AG, Semiconductor Division, Munchen, Germany; IEDM 98-683 to IEDM 98-685						
Examiner 				Date Considered 9/28/04				
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✓		"Modern Semiconductor Device Physics," S.M. Sze, John Wiley & Sons, Chapter 4 ("Power Devices") pp.203-206, (1998)						
✓		"Modeling Optimization of Lateral High-Voltage IC Devices to Minimize 3-D Effects," Hamza Yilmaz, R&D Engineering, Semiconductor Business Division, General Electric Company, NC, pp. 290-297						
✓		"Optimization of the Specific On-Resistance of the COOLMOS™," Chen, et al., IEEE Transactions on Electronic Devices, Vol. 48, no. 2, February 2001						
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			9/28/04					
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FOREIGN PATENT DOCUMENTS								
No.		Document No.	Date	Country	Name	Class	Sub-Class	Trans-lation
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)								
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ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18
Stylesheet Version v18.0

Title of Invention	Method of Fabricating a High-Voltage Transistor With A Multi-Layered Extended Drain Structure						
Application Number:	10/722792 						
Confirmation Number:	7244						
First Named Applicant:	Donald Disney						
Attorney Docket Number:	03692.P059DC						
Art Unit:	2818						
Examiner:	David Nhu						
Search string:	(6184555 or 6462377 or 6127703 or 5306656 or 6525372 or 6468847 or 5973360 or 5637898 or 5665994 or 4929987 or 4531173 or 6573558 or 6555873 or 6509220 or 6667213 or 6635544 or 6365932 or 4626789 or 6294818 or 5760440 or 6049108 or 5821144 or 4738936 or 5869875 or 6191447 or 4343015 or 6388286 or 6194283 or 4890144 or 6353252 or 6207994 or 5155574 or 5146298 or 4811075 or 4626879 or 4890146 or 5237193 or 5368136 or 5313082 or 5068700 or 5258636 or 20020175351 or 20020056884 or 20010015459).pn.						
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Note: Applicant is not required to submit a paper copy of cited US Patent Documents							
Init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
1	6184555	2001-02-06		Tihanyi et al.	B1		
2	6462377	2002-10-08		Hurky et al.	B2		
3	6127703	2000-10-03		Letavic et al.			
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5	6525372	2003-02-25		Baliga	B2		
6	6468847	2002-10-22		Disney	B1		
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9	5665994	1997-09-09		Palara			

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	11	4531173	1985-07-23	Yamada	
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	14	6509220	2003-01-21	Disney	B2
	15	6667213	2003-12-23	Disney	B2
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	40	5068700	1991-11-26	Yamaguchi et al.	
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Note: Applicant is not required to submit a paper copy of cited US Published Applications

(01722,792

init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
P2	1	20020175351	2002-11-28	Baliga	A1		
	2	20020056884	2002-05-16	Baliga	A1		
P1	3	20010015459	2001-08-23	Watanabe et al.	A1		

Signature

Examiner Name	Date
	9/28/04

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